

L Number	Hits	Search Text	DB	Time stamp
1	2113	438/458.ccls. 438/459.ccls. 438/463.ccls. 438/479.ccls. 438/940.ccls. 438/977.ccls.	USPAT; US-PGPUB	2004/07/24 19:46
3	1140	(gan (gallium adj nitride) (nitride near (compound semiconductor)) (group near2 nitride)) same laser same ((growth adj (substrate wafer)) sic (silicon adj carbide) sapphire)	USPAT; US-PGPUB	2004/07/24 19:54
5	661	(gan (gallium adj nitride) (nitride near (compound semiconductor)) (group near2 nitride)) and laser and ((growth adj (substrate wafer)) sic (silicon adj carbide) sapphire)	EPO; JPO; DERWENT; IBM_TDB	2004/07/24 19:54
2	194	(438/458.ccls. 438/459.ccls. 438/463.ccls. 438/479.ccls. 438/940.ccls. 438/977.ccls.) and (gan (gallium adj nitride) (nitride near (compound semiconductor)) (group near2 nitride))	USPAT; US-PGPUB	2004/07/24 19:55
4	174	(gan (gallium adj nitride) (nitride near (compound semiconductor)) (group near2 nitride)) same (laser with (separat\$6 remov\$6 ablat\$6)) same ((growth adj (substrate wafer)) sic (silicon adj carbide) sapphire)	USPAT; US-PGPUB	2004/07/24 20:13
7	48	(gan (gallium adj nitride) (nitride near (compound semiconductor)) (group near2 nitride)) and (laser with (separat\$6 remov\$6 ablat\$6)) and ((growth adj (substrate wafer)) sic (silicon adj carbide) sapphire)	EPO; JPO; DERWENT; IBM_TDB	2004/07/24 20:13